TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (-MOSVII)

TPCA8007-H

Switching Regulator Applications Motor Drive Applications

- Small footprint due to small and thin package
- High speed switching
- Low drain-source ON resistance

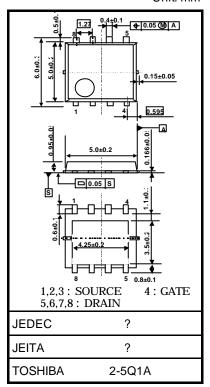
: R DS (ON) = 30 mO (typ.) (VG=10V, ID=10A)

- High forward transfer admittance: $|Y_{fs}| = 19 S$ (typ.)
- Low leakage current: IDSS = $100 \mu A \text{ (max) (VDS} = 100 \text{ V)}$
- Enhancement mode: $V_{th} = 3.0 \text{ to } 5.0 \text{ V } (V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA})$

Maximum Ratings (Ta = 25°C)

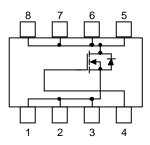
Characte	ristics	Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	100	V	
Drain-gate voltage (F	$R_{GS} = 20 \text{ k}\Omega$	V_{DGR}	100	V	
Gate-source voltage		V_{GSS}	±20	V	
Drain current	DC (Note 1)	l _D	20	А	
Diam current	Pulsed (Note 1)	l _{DP}	40	Α	
Drain power dissipation	on (Tc=25)	P_{D}	45	W	
Drain power dissipation	on $(t = 10 s)$ (Note 2a)	P_{D}	2.8	W	
Drain power dissipation	on $(t = 10 s)$ (Note 2b)	P_{D}	1.6	W	
Single pulse avalanch	ne energy (Note 3)	E _{AS}	351	mJ	
Avalanche current		I _{AR}	20	Α	
Repetitive avalanche (N	energy ote 2a) (Note 4)	E _{AR}	4.5	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature	range	T _{stg}	-55 to 150	°C	

Unit: mm



Weight: 0.080 g (typ.)

Circuit Configuration



Note: For (Note 1), (Note 2), (Note 3), (Note 4), please refer to the next page.

This transistor is an electrostatic sensitive device. Please handle with caution.

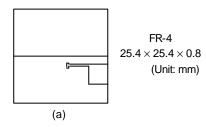
Thermal Characteristics

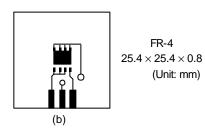
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case (Tc=25)	R _{th (ch-c)}	2.78	°C/W
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2a)	R _{th (ch-a)}	44.6	°C/W
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2b)	R _{th (ch-a)}	78.1	°C/W

Note 1: Please use devices on condition that the channel temperature is below 150 °C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)





Note 3: $V_{DD} = 50 \text{ V}$, $T_{ch} = 25^{\circ}\text{C}$ (initial) , L = 1.0 mH , $R_G = 25 \,\Omega$, $I_{AR} = 20 \text{ A}$

Note 4: Repetitive rating: pulse width limited by max channel temperature

TENTATIVE

Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		l _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA
Drain cut-OFF cu	ırrent	I _{DSS}	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$	_	_	100	μΑ
Drain-source brea	akdown voltage	V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	100	_	_	V
Gate threshold vo	oltage	V _{th}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	3.0	_	5.0	V
Drain-source ON	l resistance	R _{DS (ON)}	$V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	_	30	47	mΩ
Forward transfer	admittance	Y _{fs}	$V_{DS} = 10 \text{ V}, I_D = 10 \text{ A}$	9.5	19	_	S
Input capacitance		C _{iss}		_	1000	_	pF
Reverse transfer capacitance		C _{rss}	$V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz$	_	21	_	
Output capacitance		C _{oss}		_	500	_	
Switching time	Rise time	t _r	V _{GS} 10 V I _D = 10 A O V _{OUT} G _S I _S	_	(2)	_	
	Turn-ON time	t _{on}		_	(13)	_	
	Fall time	t _f		_	3	_	ns
	Turn-OFF time	t _{off}	$V_{DD} \simeq 50 \text{ V}$ Duty $\leq 1\%$, $t_w = 10 \mu\text{s}$	_	13	_	
Total gate charge (gate-source plus gate-drain)		Qg			15		
Gate-source charge 1		Q _{gs1}	$V_{DD} \approx 80 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$		7.2		nC
Gate-drain ("miller") charge		Q _{gd}		_	5.0		
Gate switch char	Gate switch charge]	_	8.5		

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current P	Pulse (tw=1ms)	I _{DRP}	_	_	_	40	Α
Forward voltage (diode)		V_{DSF}	$I_{DR} = 20 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	-1.7	V

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